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Vishay Siliconix

# Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.007				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.011				
I <sub>D</sub> (A)	- 50				
Configuration	Single				

#### **FEATURES**





• 100 % R<sub>g</sub> and UIS Tested

Material categorization:
For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>





ROHS COMPLIANT HALOGEN FREE

TO-252		s o
G D S	Drain Connected to Tab	G
Top View		P-Channel MOSFET

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P03-07-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	- 30	V	
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	1	- 50		
	T <sub>C</sub> = 125 °C	l <sub>D</sub>	- 50		
Continuous Source Current (Diode Conduction) <sup>a</sup>	Continuous Source Current (Diode Conduction) <sup>a</sup>			Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 50		
Single Pulse Avalanche Energy		E <sub>AS</sub>	125	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	136	W	
	T <sub>C</sub> = 125 °C		45	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	1.1		

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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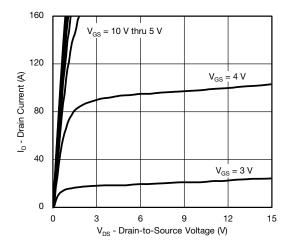
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0, I <sub>D</sub> = - 250 μA		- 30	-	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		- 2.0	- 2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 30 V	-	-	- 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 125 °C	-	-	- 50	μA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = - 30 V, T <sub>J</sub> = 175 °C	-	-	- 250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le -5 V$	- 50	-	-	Α
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 20 A	-	0.005	0.007	
Dunin Course On Otata Basistanas	Б	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 20 A, T <sub>J</sub> = 125 °C	-	-	0.011	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 20 A, T <sub>J</sub> = 175 °C	-	-	0.012	Ω
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 15 A	-	0.008	0.011	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> =	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 20 A		52	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	4390	5490	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = - 25 V, f = 1 MHz	-	766	960	
Reverse Transfer Capacitance	C <sub>rss</sub>	7		-	672	840	
Total Gate Charge <sup>c</sup>	Qg			-	97	146	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -75 \text{ A}$	-	7.6	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	7		-	29.1	-	
Gate Resistance	Rg	f = 1 MHz		1.40	2.85	4.50	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	11	17	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 15 V, $R_L$ = 0.2 $\Omega$ $I_D \cong$ - 75 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		-	12	18	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	63	95	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	28	42	
Source-Drain Diode Ratings and Char-	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	- 200	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = - 30 A, V <sub>GS</sub> = 0		-	- 0.85	- 1.5	V

#### Notes

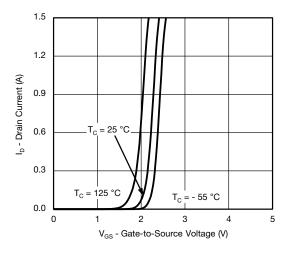
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

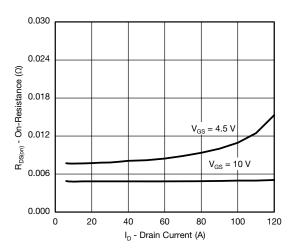
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### **Output Characteristics**

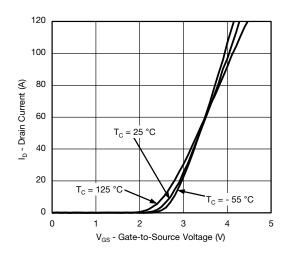


#### **Transfer Characteristics**

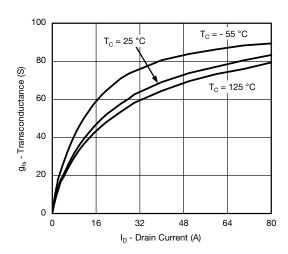


On-Resistance vs. Drain Current

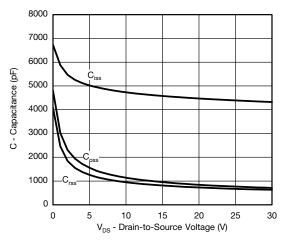
S12-1848-Rev. B, 30-Jul-12



#### **Transfer Characteristics**



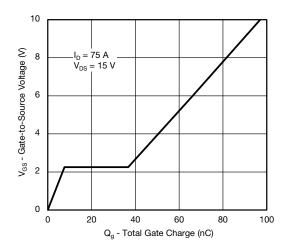
#### Transconductance



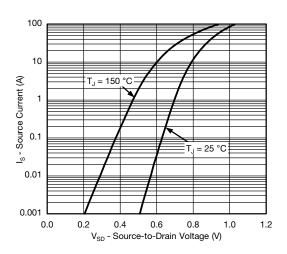
Capacitance



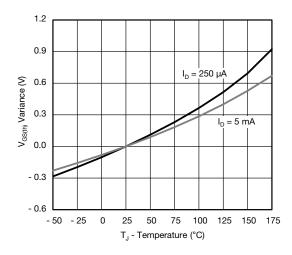
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



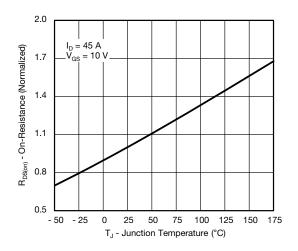
#### **Gate Charge**



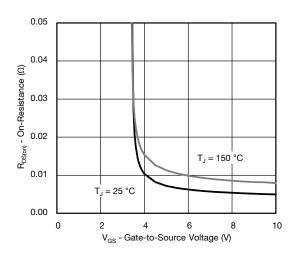
### Source Drain Diode Forward Voltage



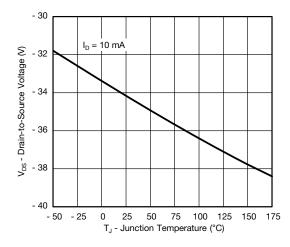
**Threshold Voltage** 



On-Resistance vs. Junction Temperature

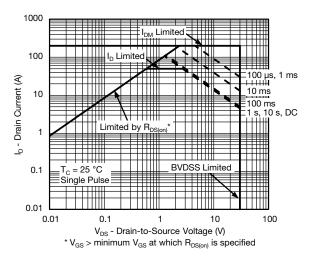


On-Resistance vs. Gate-to-Source Voltage

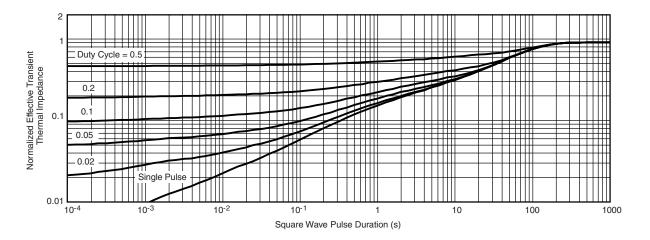


Drain Source Breakdown vs. Junction Temperature

# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



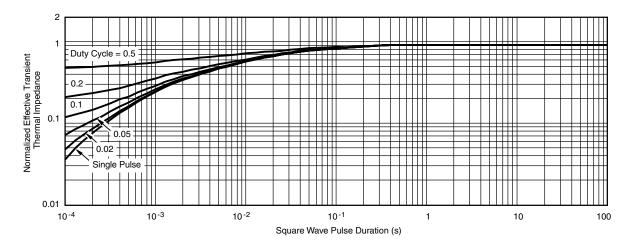
#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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# THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

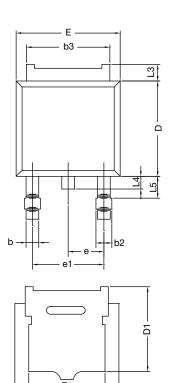
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

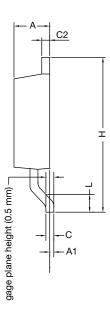
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg267014">www.vishay.com/ppg267014</a>.



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# **TO-252AA Case Outline**





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180	BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13					

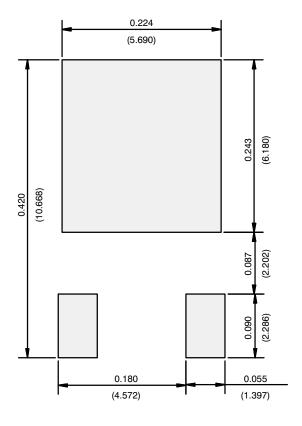
#### DWG: 6019

Note

• Dimension L3 is for reference only.



# **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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